

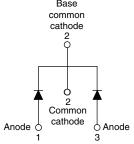
www.vishay.com

Vishay Semiconductors

# Hyperfast Rectifier, 2 x 15 A FRED Pt®



**TO-220AB** 



Dase	
common	
cathode	
2	
φ	
* 0 *	
<b>↑</b> 2 <b>↑</b>	
Common	

#### **FEATURES**

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Designed and qualified according to JEDEC®-JESD 47







HALOGEN **FREE** 

PRODUCT SUMMARY					
Package	TO-220AB				
I <sub>F(AV)</sub>	2 x 15 A				
V <sub>R</sub>	300 V				
V <sub>F</sub> at I <sub>F</sub>	0.85 V				
t <sub>rr</sub> typ.	See Recovery table				
T <sub>J</sub> max.	175 °C				
Diode variation	Common cathode				

## **DESCRIPTION / APPLICATIONS**

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage		$V_{RRM}$		300	V			
Average rectified forward current	per diode	I <sub>E(A\A</sub>	T <sub>C</sub> = 153 °C	15				
	per device			30	Α			
Non-repetitive peak surge current		I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	150				
Operating junction and storage temp	oeratures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN. TYP. MAX				
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	300	-	-		
Forward voltage V <sub>F</sub>	V-	I <sub>F</sub> = 15 A	-	1.0	1.25	V	
	٧F	I <sub>F</sub> = 15 A, T <sub>J</sub> = 125 °C	-	0.85	0.95		
Doverno lookogo overnost	1	$V_R = V_R$ rated	-	-	40		
Reverse leakage current I <sub>R</sub>		$T_J = 125  ^{\circ}C$ , $V_R = V_R$ rated	-	8	200	μΑ	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 300 V	-	38	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH	



## www.vishay.com

# Vishay Semiconductors

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)																
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS										
		$I_F = 1 A, dI_F/dt = 50$	$0 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	-	-	36										
Payeras rassyony time		$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	30	20									
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	33	-	ns									
		T <sub>J</sub> = 125 °C		-	48	-										
Dook receivery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	$I_F = 15 \text{ A}$	-	2.8	-	Α									
Peak recovery current		IRRM	IRRM	IRRM	IRRM	IRRM	IRRM	IRRM	IRRM	IRRM	$T_{\rm J} = 125^{\circ}$	T <sub>J</sub> = 125 °C	$dI_F/dt = 200 A/\mu s$ $V_B = 200 V$	-	6.5	-
D	0	T <sub>J</sub> = 25 °C	vH - 200 v	=	46	-	.0									
Reverse recovery charge	$Q_{rr}$	T <sub>J</sub> = 125 °C		-	160	-	nC									

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>	-65	=	175	°C		
Thermal resistance, junction to case per diode	$R_{thJC}$	-	-	1.4	°C/W		
Marking device		Case style TO-220AB		30C	ГН03		

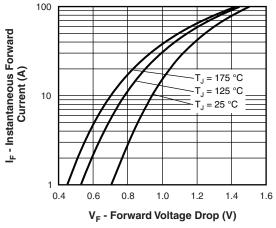


Fig. 1 - Typical Forward Voltage Drop Characteristics

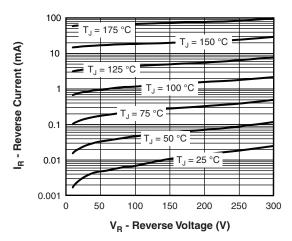


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

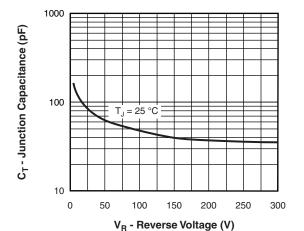


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

www.vishay.com

## Vishay Semiconductors

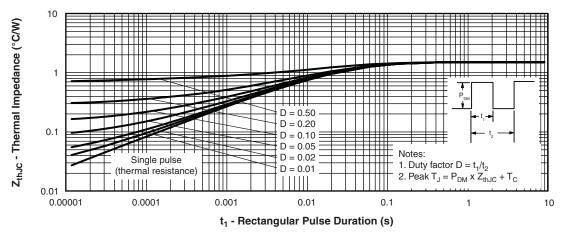


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

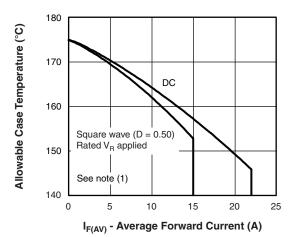


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

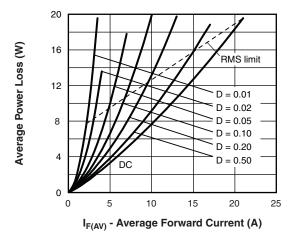


Fig. 6 - Forward Power Loss Characteristics

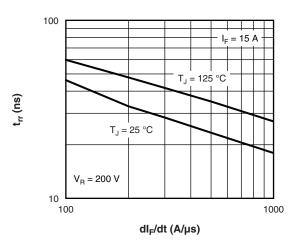


Fig. 7 - Typical Reverse Recovery Time vs.  $dI_{\text{F}}/dt$ 

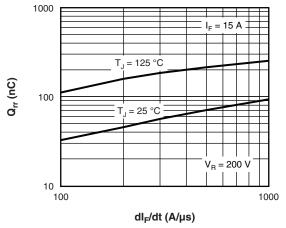


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

## Note

<sup>(1)</sup> Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>th,JC</sub>; Pd = Forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 6); Pd<sub>REV</sub> = Inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = Rated V<sub>R</sub>

# Vishay Semiconductors

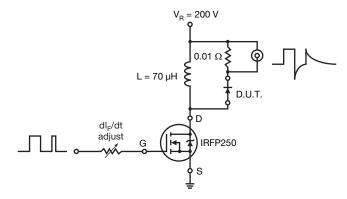
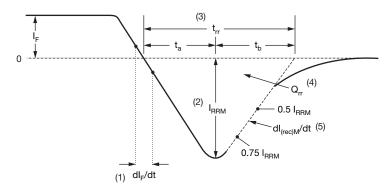


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) dI<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

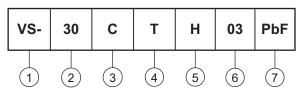
Fig. 10 - Reverse Recovery Waveform and Definitions

# VS-30CTH03PbF, VS-30CTH03-N3

Vishay Semiconductors

## **ORDERING INFORMATION TABLE**

**Device code** 



Vishay Semiconductors product

2 - Current rating (30 = 30 A)

Circuit configuration:

C = common cathode

4 - Package:

T = TO-220

5 - H = hyperfast recovery

Voltage rating (03 = 300 V)

7 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-30CTH03PbF	50	1000	Antistatic plastic tube					
VS-30CTH03-N3	50	1000	Antistatic plastic tube					

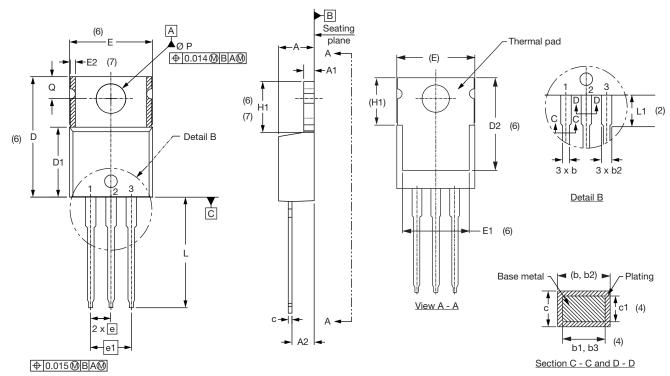
LINKS TO RELATED DOCUMENTS						
Dimensions	TO-220AB	www.vishay.com/doc?95222				
Deut eranding information	TO-220ABPbF	www.vishay.com/doc?95225				
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028				



## Vishay Semiconductors

## **TO-220AB**

## **DIMENSIONS** in millimeters and inches



# Lead tip

## Lead assignments

## <u>Diodes</u>

- 1. Anode/open
- 2. Cathode
- 3. Anode

## Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INCHES		NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Е	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° to 93°		

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



## **Legal Disclaimer Notice**

Vishay

## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.